

# MOSFET – Power, Single, P-Channel

**-60 V, -61 A, 16 mΩ**

## NVD5117PL

### Features

- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- High Current Capability
- Avalanche Energy Specified
- AEC-Q101 Qualified
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter			Value	Unit
V <sub>DSS</sub>	Drain-to-Source Voltage			-60	V
V <sub>GS</sub>	Gate-to-Source Voltage			± 20	V
I <sub>D</sub>	Continuous Drain Current R <sub>θJC</sub> (Note 1)	Steady State	T <sub>C</sub> = 25°C	-61	A
			T <sub>C</sub> = 100°C	-43	
P <sub>D</sub>	Power Dissipation R <sub>θJC</sub> (Note 1)		T <sub>C</sub> = 25°C	118	W
			T <sub>C</sub> = 100°C	59	
I <sub>D</sub>	Continuous Drain Current R <sub>θJA</sub> (Notes 1 & 2)	Steady State	T <sub>A</sub> = 25°C	-11	A
			T <sub>A</sub> = 100°C	-8	
P <sub>D</sub>	Power Dissipation R <sub>θJA</sub> (Notes 1 & 2)		T <sub>A</sub> = 25°C	4.1	W
			T <sub>A</sub> = 100°C	2.1	
I <sub>DM</sub>	Pulsed Drain Current	T <sub>A</sub> = 25°C, t <sub>p</sub> = 10 μs		-419	A
I <sub>Dmaxpkg</sub>	Current Limited by Package (Note 3)	T <sub>A</sub> = 25°C		60	A
T <sub>J</sub> , T <sub>stg</sub>	Operating Junction and Storage Temperature			-55 to 175	°C
I <sub>S</sub>	Source Current (Body Diode)			-118	A
E <sub>AS</sub>	Single Pulse Drain-to-Source Avalanche Energy (T <sub>J</sub> = 25°C, V <sub>DD</sub> = 50 V, V <sub>GS</sub> = 10 V, I <sub>L(pk)</sub> = 40 A, L = 0.3 mH, R <sub>G</sub> = 25 Ω)			240	mJ
T <sub>L</sub>	Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			260	°C

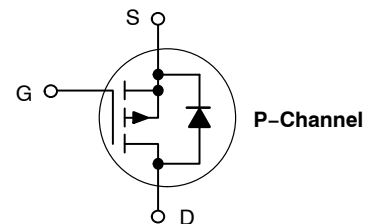
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL RESISTANCE MAXIMUM RATINGS

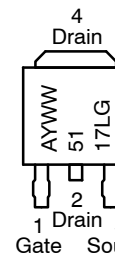
Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Junction-to-Case – Steady State (Drain)	1.3	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Junction-to-Ambient – Steady State (Note 2)	37	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$
-60 V	16 mΩ @ -10 V 22 mΩ @ -4.5 V	-61 A



### MARKING DIAGRAMS & PIN ASSIGNMENT



A = Assembly Location\*  
Y = Year  
WW = Work Week  
5117L = Device Code  
G = Pb-Free Package

\* The Assembly Location Code (A) is front side optional. In cases where the Assembly Location is stamped in the package bottom (molding ejector pin), the front side assembly code may be blank.

### ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 5.

# NVD5117PL

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA	-60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = -60 V	T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C		-1.0 -100	μA
I <sub>GSS</sub>	Gate-to-Source Leakage Current	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA

### ON CHARACTERISTICS (Note 4)

V <sub>GS(TH)</sub>	Gate Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = -250 μA	-1.5		-2.5	V
R <sub>DS(on)</sub>	Drain-to-Source On Resistance	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -29 A V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -29 A		12 16	16 22	mΩ
g <sub>FS</sub>	Froward Transconductance	V <sub>DS</sub> = -15 V, I <sub>D</sub> = -15 A		30		S

### CHARGES AND CAPACITANCES

C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0 V, f = 1.0 MHz, V <sub>DS</sub> = -25 V		4800		pF
C <sub>oss</sub>	Output Capacitance			480		
C <sub>rss</sub>	Reverse Transfer Capacitance			320		
Q <sub>G(TOT)</sub>	Total Gate Charge	V <sub>DS</sub> = -48 V, I <sub>D</sub> = -29 A	V <sub>GS</sub> = -4.5 V V <sub>GS</sub> = -10 V	49 85		nC
Q <sub>G(TH)</sub>	Threshold Gate Charge	V <sub>GS</sub> = -4.5 V, V <sub>DS</sub> = -48 V, I <sub>D</sub> = -29 A		3		
Q <sub>GS</sub>	Gate-to-Source Charge			13		
Q <sub>GD</sub>	Gate-to-Drain Charge			28		
V <sub>GP</sub>	Plateau Voltage			3.2		V

### SWITCHING CHARACTERISTICS (Notes 4)

t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>GS</sub> = -4.5 V, V <sub>DS</sub> = -48 V, I <sub>D</sub> = -29 A, R <sub>G</sub> = 2.5 Ω		22		ns
t <sub>r</sub>	Rise Time			195		
t <sub>d(off)</sub>	Turn-Off Delay Time			50		
t <sub>f</sub>	Fall Time			132		

### DRAIN-SOURCE DIODE CHARACTERISTICS

V <sub>SD</sub>	Forward Diode Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -29 A	T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C	-0.86 -0.74	-1.0	V
t <sub>RR</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, dI <sub>S</sub> /dt = 100 A/μs, I <sub>S</sub> = -29 A		36		ns
t <sub>a</sub>	Charge Time			19		
t <sub>b</sub>	Discharge Time			17		
Q <sub>RR</sub>	Reverse Recovery Charge			44		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS

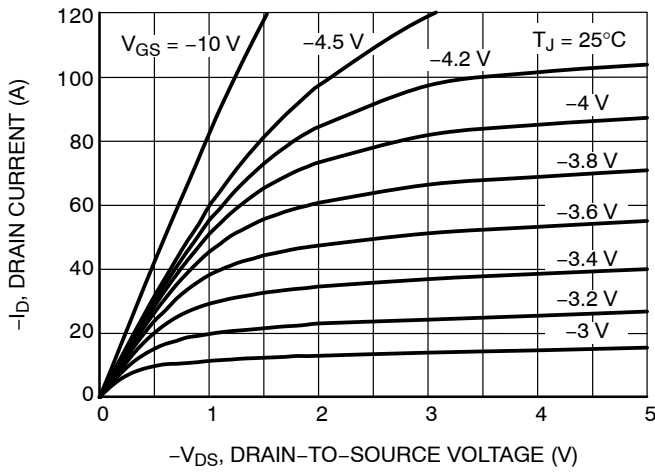


Figure 1. On-Region Characteristics

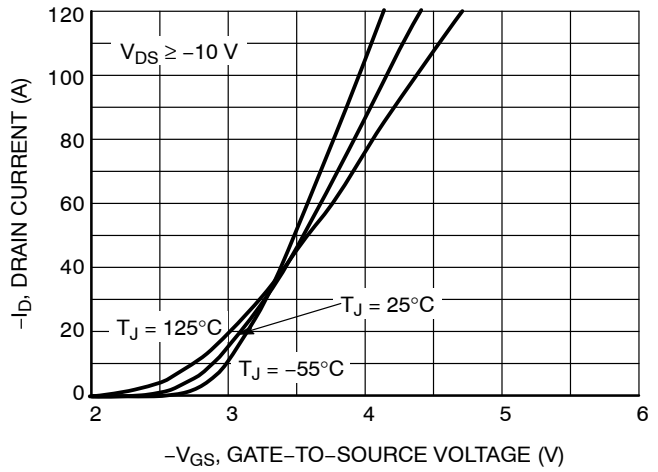


Figure 2. Transfer Characteristics

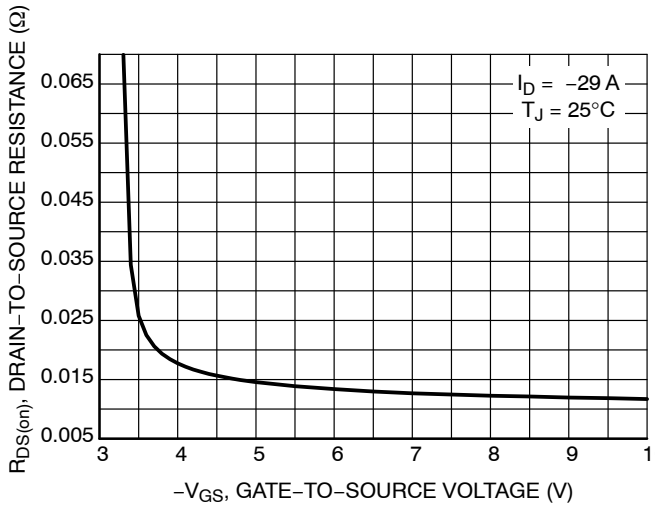


Figure 3. On-Resistance vs. Gate-to-Source Voltage

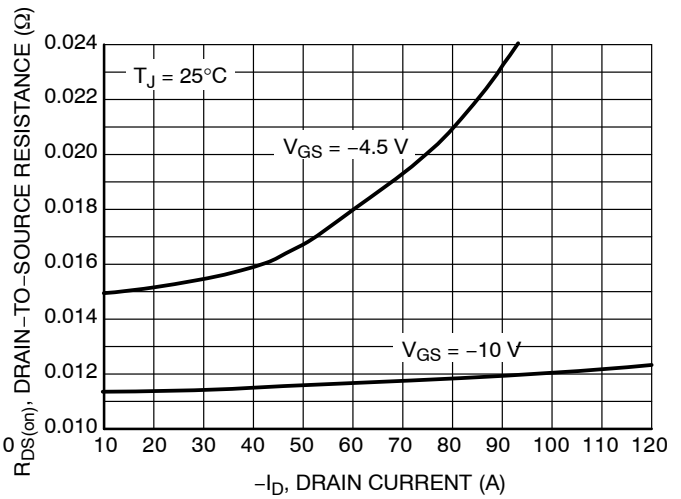


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

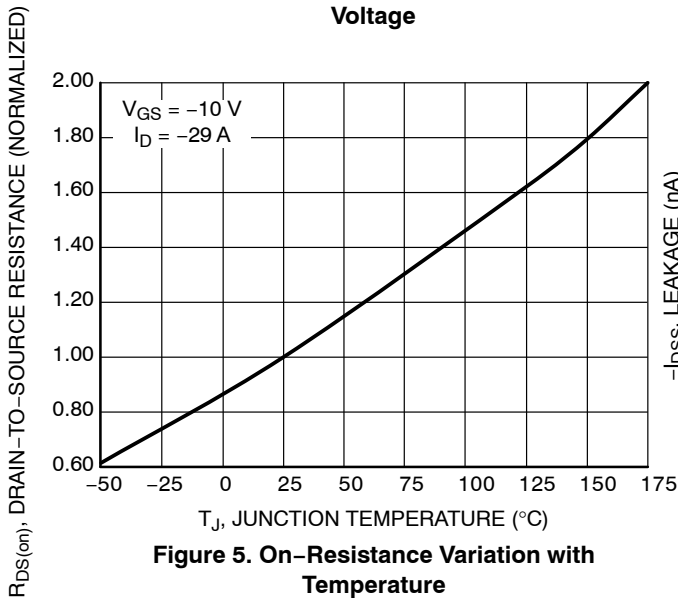


Figure 5. On-Resistance Variation with Temperature

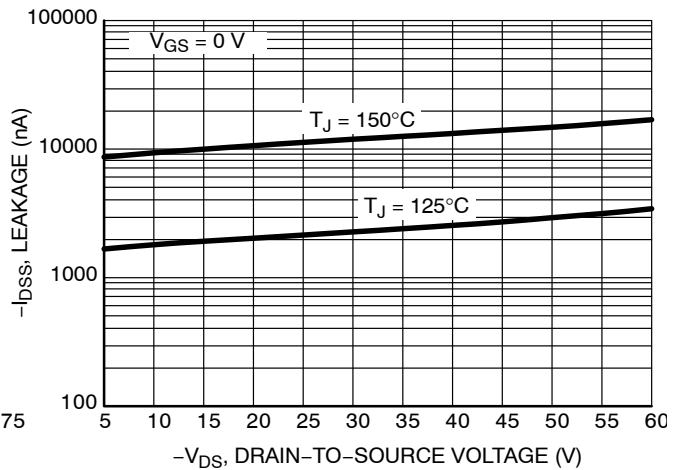


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS (continued)

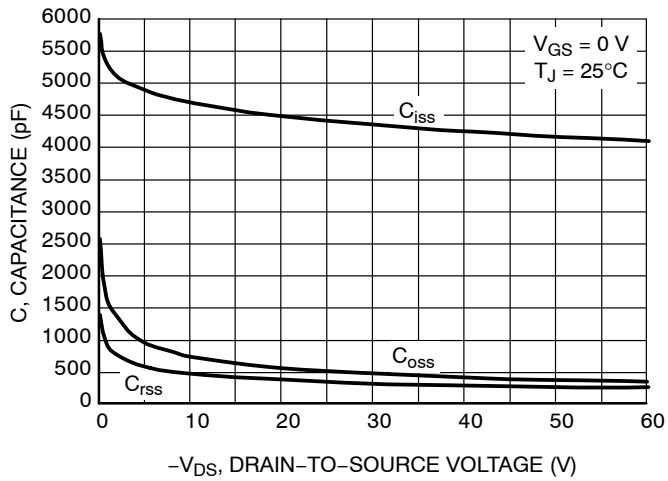


Figure 7. Capacitance Variation

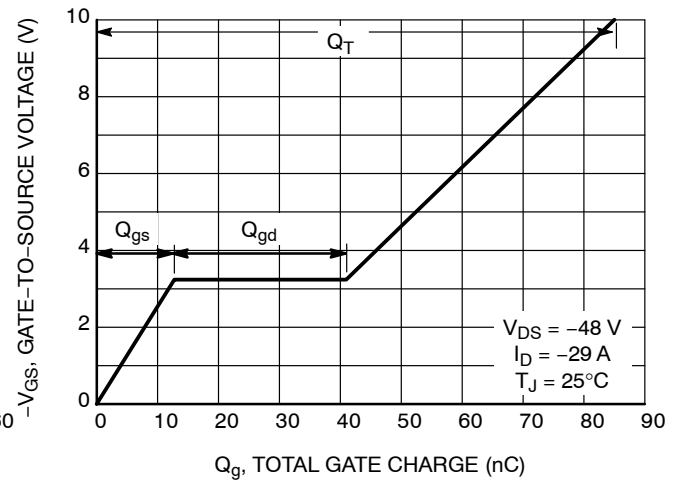


Figure 8. Gate-to-Source vs. Total Charge

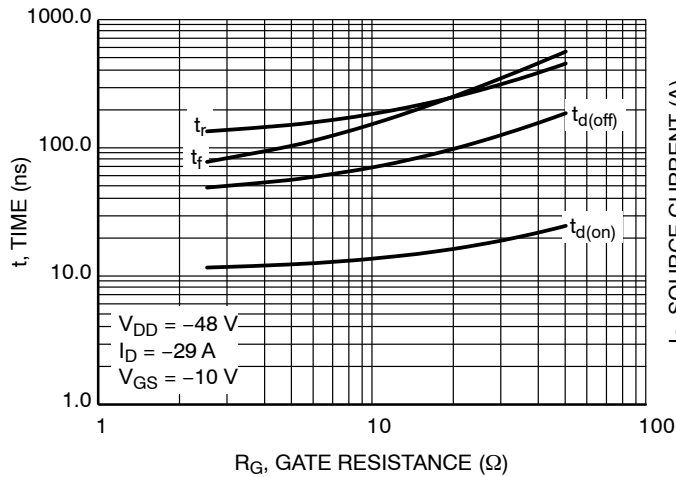


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

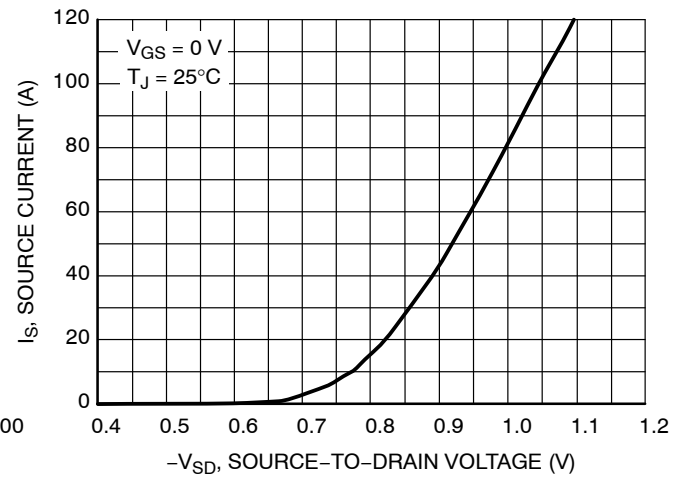


Figure 10. Diode Forward Voltage vs. Current

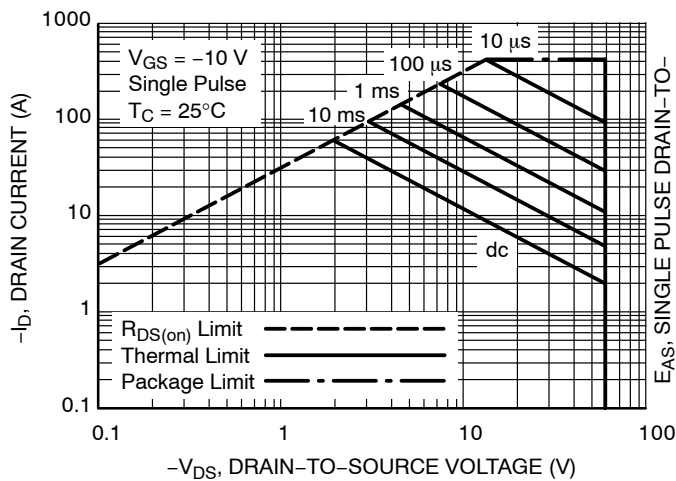


Figure 11. Maximum Rated Forward Biased Safe Operating Area

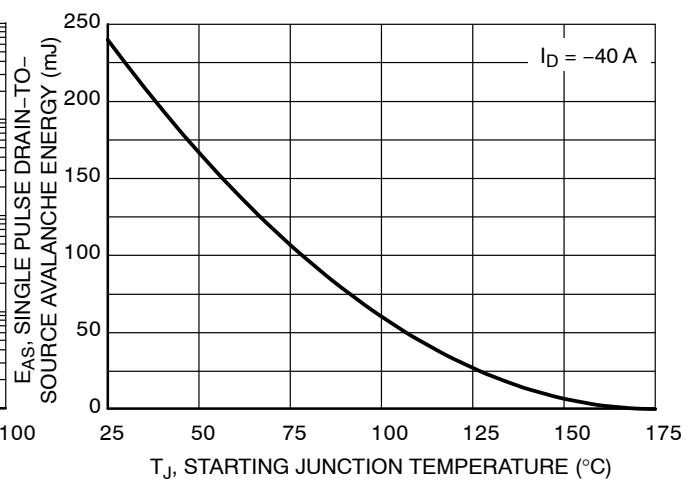


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

# NVD5117PL

## TYPICAL CHARACTERISTICS (continued)

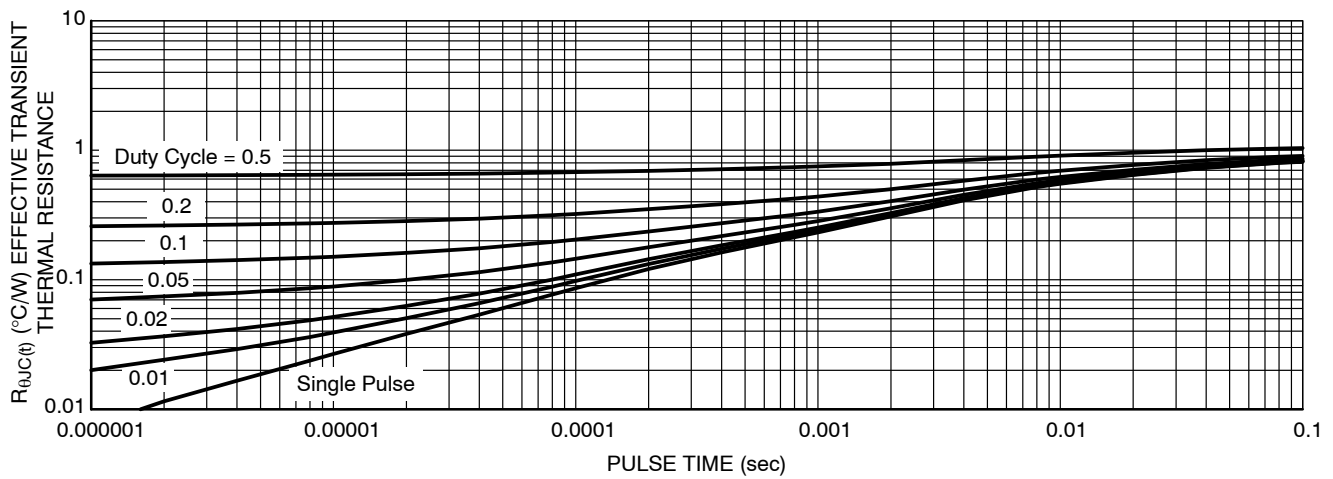


Figure 13. Thermal Response

### DEVICE ORDERING INFORMATION

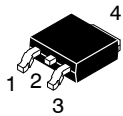
Device	Package	Shipping <sup>†</sup>
NVD5117PLT4G-VF01	DPAK (Pb-Free)	2500 / Tape & Reel

### DISCONTINUED (Note 5)

NVD5117PLT4G	DPAK (Pb-Free)	2500 / Tape & Reel
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<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

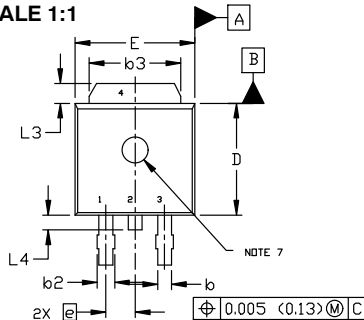
5. **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on [www.onsemi.com](http://www.onsemi.com).



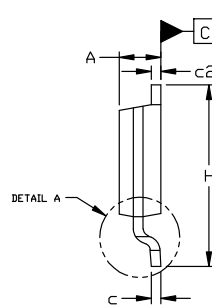
DPAK (SINGLE GAUGE)  
CASE 369C  
ISSUE G

DATE 31 MAY 2023

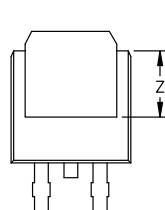
SCALE 1:1



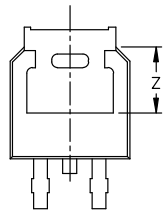
TOP VIEW



SIDE VIEW

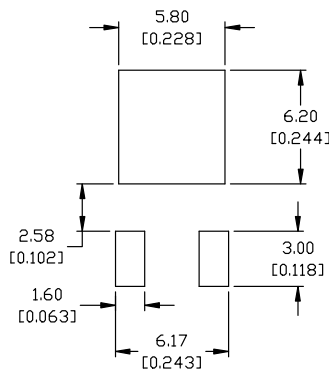


BOTTOM VIEW



BOTTOM VIEW

ALTERNATE  
CONSTRUCTIONS



RECOMMENDED MOUNTING FOOTPRINT\*

\*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

STYLE 1:

PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 2:

PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN

STYLE 3:

PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. CATHODE

STYLE 4:

PIN 1. CATHODE  
2. ANODE  
3. GATE  
4. ANODE

STYLE 5:

PIN 1. GATE  
2. ANODE  
3. CATHODE  
4. ANODE

STYLE 6:

PIN 1. MT1  
2. MT2  
3. GATE  
4. MT2

STYLE 7:

PIN 1. GATE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 8:

PIN 1. N/C  
2. CATHODE  
3. ANODE  
4. CATHODE

STYLE 9:

PIN 1. ANODE  
2. CATHODE  
3. RESISTOR ADJUST  
4. CATHODE

STYLE 10:

PIN 1. CATHODE  
2. ANODE  
3. CATHODE  
4. ANODE

NOTES:

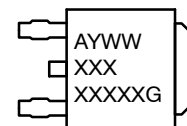
- DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: INCHES
- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
- DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
- OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29	BSC
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4	----	0.040	---	1.01
Z	0.155	----	3.93	---

GENERIC  
MARKING DIAGRAM\*



IC



Discrete

XXXXXX = Device Code  
A = Assembly Location  
L = Wafer Lot  
Y = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	DPAK (SINGLE GAUGE)	PAGE 1 OF 1

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[www.onsemi.com/support/sales](http://www.onsemi.com/support/sales)